

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	400mΩ@-4.5V	-0.75A
	550mΩ@-2.5V	

Feature

- Surface Mount Package
- P-Channel Switch with Low RDS(on)
- Operated at Low Logic Level Gate Drive
- ESD Protected

Applications

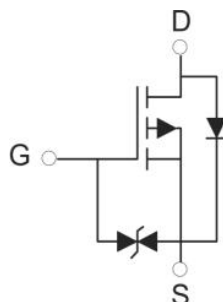
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics

Package



PDFN1212-3L

Circuit diagram



Marking



04K =Device Code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±10	V
Continuous Drain Current (T _A =25°C, silicon limited)	I _D	-0.75	A
Continuous Drain Current (T _A =25°C, Package limited)	I _D	-0.6	A
Continuous Drain Current (T _A =100°C, silicon limited)	I _D	-0.5	A
Pulsed Drain Current	I _{DM}	-3	A
Power Dissipation	P _D	0.42	W
Thermal Resistance from Junction to Ambient	R _{θJA}	297	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG.}	-55~ +150	°C

Electrical characteristics

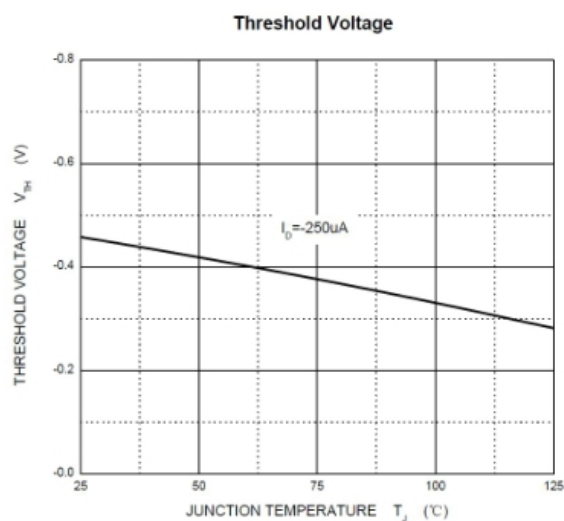
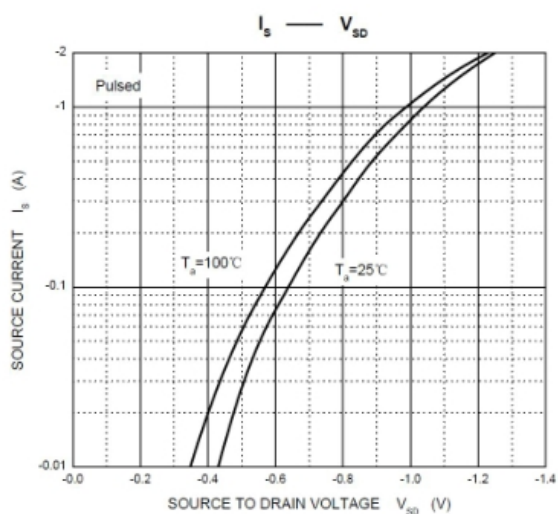
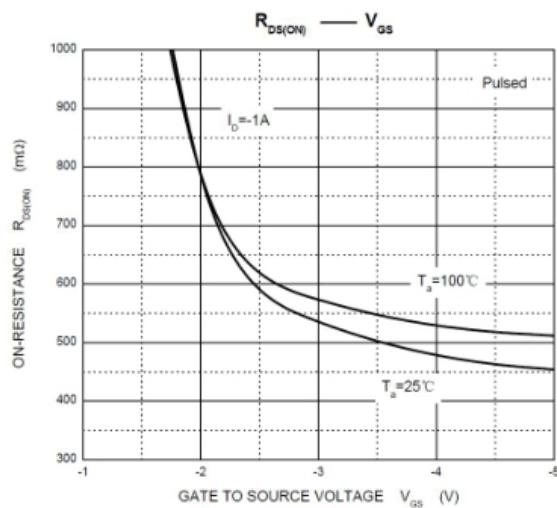
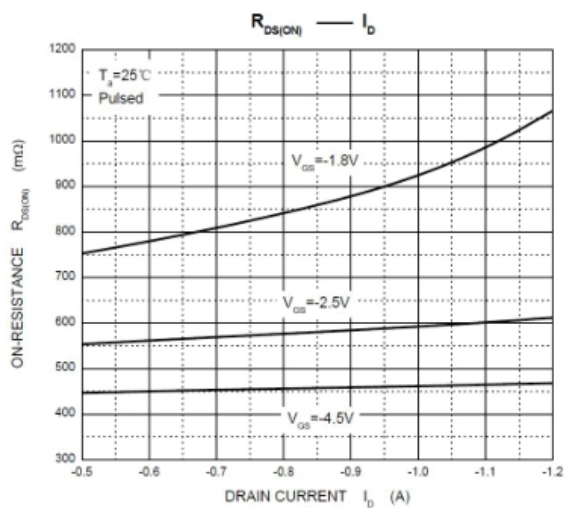
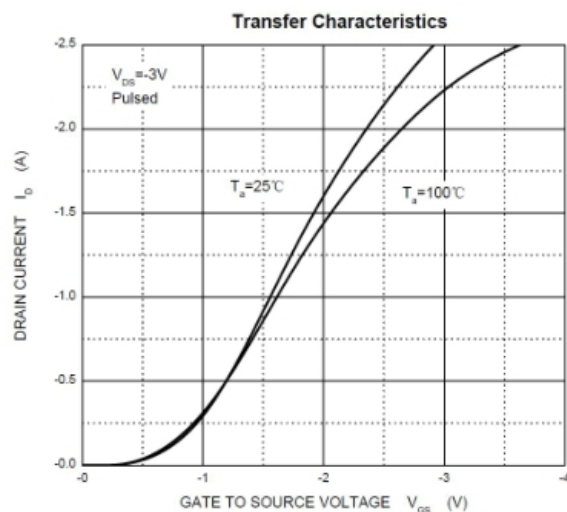
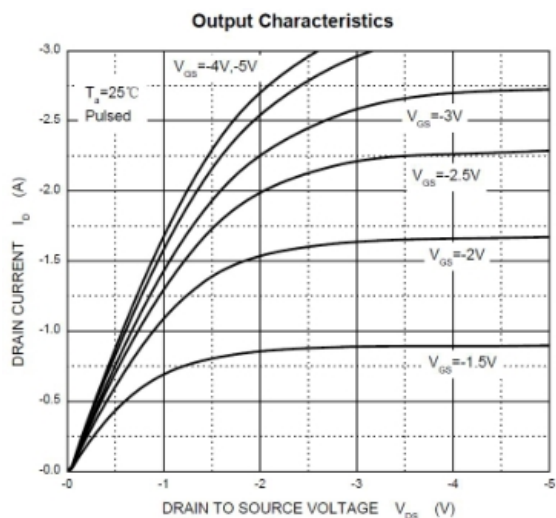
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1	uA
Gate-body leakage current	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V			±10	uA
Gate threshold voltage ⁽¹⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D = -250μA	-0.35	-0.65	-1	V
Drain-source on-resistance ⁽¹⁾	R _{DS(on)}	V _{GS} = -4.5V, I _D = -0.5A		0.4	0.55	Ω
		V _{GS} = -2.5V, I _D = -0.2A		0.55	0.7	
Dynamic Characteristics						
Input capacitance	C _{iss}	V _{DS} = -16V, V _{GS} =0V, f=1MHz		113		pF
Output capacitance	C _{oss}			15		
Reverse transfer capacitance	C _{rss}			9		
Turn-on Delay Time	T _{d(on)}	V _{DS} = -10V, I _D =200mA , V _{GS} = -4.5V, R _{GEN} =10Ω		9		nS
Turn-on Rise Time	T _r			5.7		
Turn-Off Delay Time	T _{d(off)}			32.6		
Turn-Off Fall Time	t _f			20.3		
Source-Drain Diode Characteristics						
Diode Forward voltage	V _{SD}	I _S = -0.5A, V _{GS} = 0V			-1.2	V

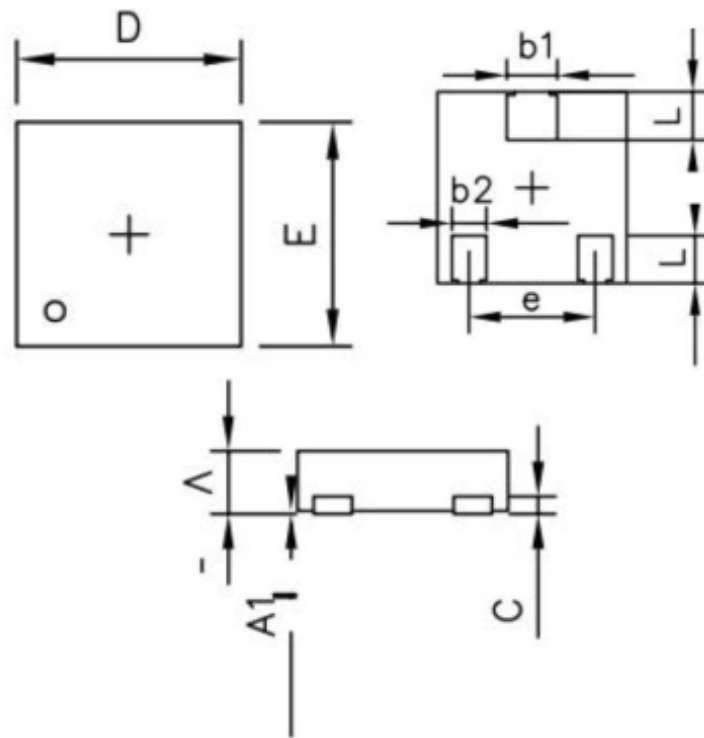
Notes:

1. Pulse Test: Pulse Width $< 300\mu s$, Duty Cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production testing.

Typical Characteristics



PDFN1212-3L Package Information



PDFN1212-3L POD				
Dimension		Min(mm)	TYP(mm)	Max (mm)
Symbol				
A		0.45	0.50	0.55
A1		0.00	0.03	0.05
C		0.152		
b1		0.27	0.32	0.37
L		0.25	0.30	0.35
D		1.15	1.20	1.25
e		0.80		
E		1.15	1.20	1.25
b2		0.17	0.22	0.27